



DXT3904

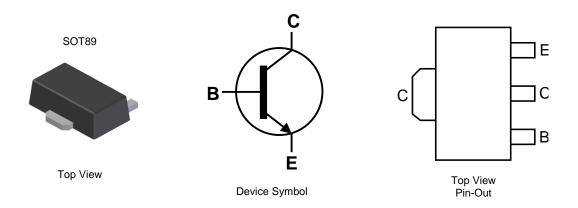
40V NPN SMALL SIGNAL TRANSISTOR IN SOT89

Features

- BV_{CEO} > 40V
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DXT3906)
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208@3
- Weight: 0.072 grams (Approximate)



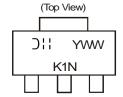
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT3904-13	AEC-Q101	K1N	13	12	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K1N = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year ex: 4 = 2014 WW = Week Code 01 - 52



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current – Continuous	Ic	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	0.75	· w	
Power Dissipation	(Note 6)	P _D	1.2		
Thermal Resistance, Junction to Ambient Air	(Note 5)	D	166	°C/W	
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{\theta JA}$	104		
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

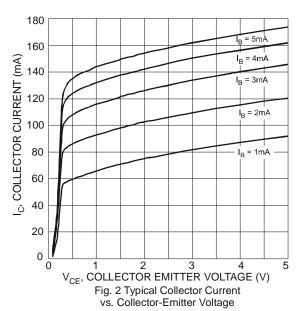
- 5. For a device mounted with the exposed collector pad on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as note (5), except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.
- 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

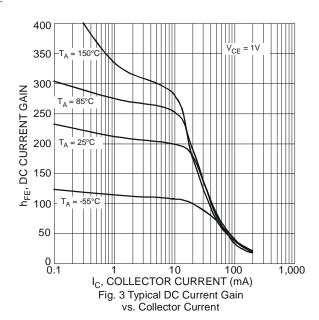


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

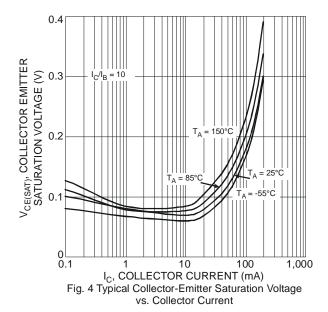
Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						
Collector-Base Breakdown Voltage	BV _{CBO}	60		V	$I_C = 10\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	BV _{CEO}	40		V	$I_C = 1.0 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0		V	$I_E = 10\mu A, I_C = 0$	
Collector Cutoff Current	I _{CEX}	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
Base Cutoff Current	I _{BL}	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
ON CHARACTERISTICS (Note 7)						
DC Current Gain	h _{FE}	40 70 100 60 30	300 —	_	$\begin{split} & I_{C} = 100 \mu A, \ V_{CE} = 1.0 V \\ & I_{C} = 1.0 mA, \ V_{CE} = 1.0 V \\ & I_{C} = 10 mA, \ V_{CE} = 1.0 V \\ & I_{C} = 50 mA, \ V_{CE} = 1.0 V \\ & I_{C} = 100 mA, \ V_{CE} = 1.0 V \end{split}$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.20 0.30	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$	
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65	0.85 0.95	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{obo}	_	4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$	
Input Capacitance	C _{ibo}	_	8.0	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_C = 0$	
Input Impedance	h _{ie}	1.0	10	kΩ		
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz	
Small Signal Current Gain	h _{fe}	100	400	_	VCE = 10V, IC = 1.0IIIA, I = 1.0KHZ	
Output Admittance	h _{oe}	1.0	40	μS		
Current Gain-Bandwidth Product	f _T	300		MHz	$V_{CE} = 20V, I_{C} = 10mA, f = 100MHz$	
Noise Figure	NF	_	5.0	dB	$V_{CE} = 5.0V, I_C = 100\mu A,$ $R_S = 1.0k\Omega, f = 1.0kHz$	
SWITCHING CHARACTERISTICS						
Delay Time	t _d		35	ns	$V_{CC} = 3.0V$, $I_{C} = 10mA$, $V_{BE(off)} = -0.5V$, $I_{B1} = 1.0mA$	
Rise Time	t _r		35	ns		
Storage Time	ts		200	ns	$V_{CC} = 3.0V, I_C = 10mA,$ $I_{B1} = -I_{B2} = 1.0mA$	
Fall Time	t _f		50	ns		

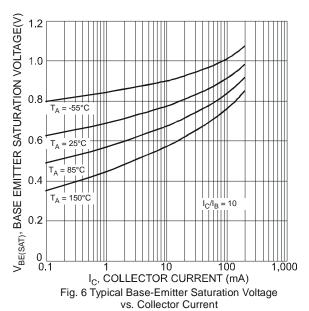
Notes: 7. Measured under pulsed condition. Pulse width = 300μ s. Duty cycle $\leq 2\%$.

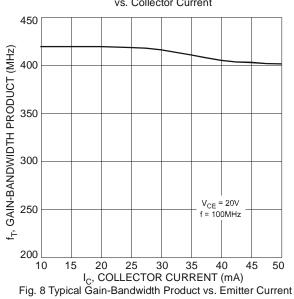


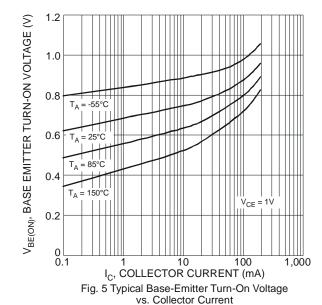


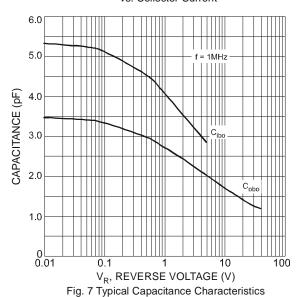








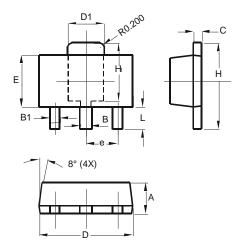






Package Outline Dimensions

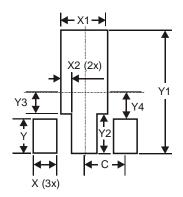
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT89					
Dim	Min	Max			
Α	1.40	1.60			
В	0.44	0.62			
B1	0.35	0.54			
C	0.35	0.44			
D	4.40	4.60			
D1	1.62	1.83			
Е	2.29	2.60			
е	e 1.50 Typ				
Н	3.94	4.25			
H1	2.63	2.93			
L	0.89	1.20			
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500



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